UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

PATENT NO.

: 6,958,296 B2

Page 1 of 2

DATED

APPLICATION NO.: 10/625480

: October 25, 2005

INVENTOR(S)

: Ling Chen, Christophe Marcadal and Hyungsuk Alexander Yoon

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the TITLE PAGE

Item [56], References Cited, U.S. PATENT DOCUMENTS: Please include the following reference:

2002/0164421

11/2002 Chiang et al.

Column 3, Line 38: Delete the first instance of "that"

Column 3, Lines 2, 3, and 21: Change each instance of "SiH4" to --SiH4--

Column 4, Lines 2, 3, and 22: Change each instance of "N2" to --N2--

Column 6, Line 39: Change "be-adjusted" to --be adjusted--

Column 6, Line 48: Change "CH3" to --CH3--

Column 7, Line 36: Change "N2" to -- N2--

Column 7, Line 44: Before "decomposed", insert --shown in FIG. 2. TDMAT is vaporized and, upon heating of the wafer, is thermally--

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Column 8, line 46: Change "TIN" to --TiN--

Column 11, Table 3: Change each instance of "SiH4" to --SiH4--

Column 11, Line 38: Change "Wafer" to --wafer--

Signed and Sealed this

Twelfth Day of September, 2006

JON W. DUDAS Director of the United States Patent and Trademark Office